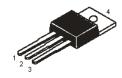
Power Transistor







Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector

Feature:

• NPN bipolar power transistors for use in high voltage, high speed transistors for horizontal deflection circuits of TVs and CRTs. Suitable for medium, high, and very high resolution monochrome and colour applications

Absolute Maximum Ratings:

Parameter	Symbol		Rating	Unit
Collector Base Voltage (Open Emitter)	V _{CBO}		330	V
Collector Emitter Voltage (Open Base)	V _{CEO}		150	V
Collector Current	I _C		7	А
Total Power Dissipation upto T _C = 25°C	P _{tot}	Max.	60	W
Junction Temperature	T _j		150	°C
Collector Emitter Saturation Voltage I _C = 5A; I _B = 0.5A	V _{CE (sat)}		1	V

Ratings (at $T_a = 25$ °C unless otherwise specified):

Parameter	Symbol		Rating	Unit
Collector Base Voltage (Open Emitter)	V _{CBO}		330	
Collector Emitter Voltage (Open Base)	V _{CEO}		150	V
Collector Emitter Voltage (V _{BE} = -1.5V)	V _{CEV}		330	V
Emitter Base Voltage (Open Collector)	V_{EBO}	Maximum	6	
Collector Current	I _C		7	
Collector Current Peak (Repetitive)			10	А
Collector Current Peak (t = 10ms)	СМ		15	





Power Transistor



Ratings (at $T_a = 25$ °C unless otherwise specified):

Parameter	Symbol		Rating	Unit
Base Current	I _B		4	А
Total Power Dissipation upto T _C = 25°C Derate above 25°C	P _{tot}	Max.	60 0.48	W W/°C
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-65 to +150	C

Thermal Resistance

From Junction to Case	R _{th (j-c)}	Ш	2.08	°C/W
From Junction to Ambient	R _{th (j-a)}	=	70	C/VV

Characteristics ($T_a = 25$ °C unless otherwise specified):

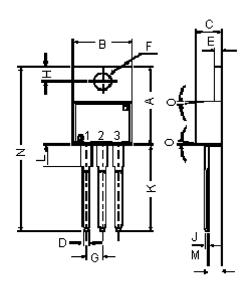
Parameter	Symbol	-	Rating	Unit
Collector Cut off Current $V_{BE} = 0$; $V_{CE} = 330V$ $V_{BE} = 0$; $V_{CE} = 200V$ $V_{BE} = 0$; $V_{CE} = 200V$; $T_{C} = 150^{\circ}C$	I _{CES}	Max.	5 100 1	mA μA mA
Emitter Cut off Current I _C = 0; V _{EB} = 6V	I _{EBO}		1	mA
Breakdown Voltages $I_C = 100 \text{mA}$; $I_B = 0$ $I_C = 1 \text{mA}$; $I_E = 0$ $I_E = 1 \text{mA}$; $I_C = 0$	V _{CEO (sus)} * V _{CBO} V _{EBO}	Min.	150 330 6	V
Saturation Voltage $I_C = 5A$; $I_B = 0.5A$	V _{CE (sat)} * V _{BE (sat)} *	Max.	1 1.2	
Transition Frequency I _C = 0.5A; V _{CE} = 10V	f _⊤	Min.	10	MHz
Switching Time $I_C = 5A$; $-I_{Bend} = 0.5A$ Turn off Time	t _{off}	Max.	0.75	μs
Second Breakdown Collector Current with Base Forward Biased V _{CE} = 40V; t = 10ms	l _{S/b}	Тур.	4	А

^{*} Pulsed: Pulse Duration = 300µs; Duty Cycle = 1.5%.



Power Transistor





Pin Configuration:

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Dimensions	Min.	Max.	
Α	14.42	16.51	
В	9.63	10.67	
С	3.56	4.83	
D	-	0.9	
E	1.15	1.4	
F	3.75	3.88	
G	2.29	2.79	
Н	2.54	3.43	
J	-	0.56	
K	12.7	14.73	
L	2.8	4.07	
M	2.03	2.92	
N	-	31.24	
0	7°		

Dimensions: Millimetres

Part Number Table

Description	Part Number	
Transistor, NPN, TO-220	BU407	

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